

Catalog # 93-1389 Aluminum iodide, 95%



## Thermal Behavior:

- Melting point: 191°C
- Boiling point: 360°C

## Technical Notes:

1. CVD precursor for aluminum nitride thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
AlN	CVD	-	AP	NH <sub>3</sub>	750°C	1

## References:

1. [Mater. Chem. Phys. 2004, 86, 74.](#)